

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Takamitsu HIGUCHI et al.

Application No.: New US Application

Filed: August 21, 2003

Docket No.: 116916

For: SUBSTRATE FOR ELECTRONIC DEVICES, MANUFACTURING METHOD
THEREFOR, AND ELECTRONIC DEVICE

INFORMATION DISCLOSURE STATEMENT

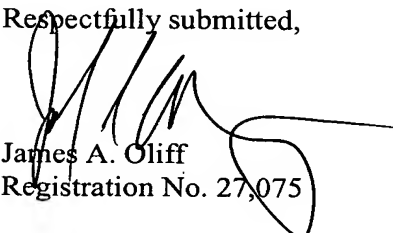
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. The present application was filed or entered the U.S. National Stage of the PCT after June 30, 2003. In accordance with the June 11, 2003, Notice waiving the requirements of 37 C.F.R. §1.98(a)(2)(i), copies of any U.S. patents and patent application publications are not attached.
- ☒ 3. English-language Abstracts of the non-English language references are attached hereto.
- ☒ 4. Computer-generated English translations of the following Japanese Patent Publications have been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and are attached, but have not been reviewed for accuracy. See References 13-27.
- ☒ 5. Relevance of the non-English language references Nos. 26 and 28-30 are discussed in the present specification.

Respectfully submitted,


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<p>DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461</p>
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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 116916		APPLICATION NO. New US Application	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Takamitsu HIGUCHI et al.			
				FILING DATE August 21, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
	1	6,232,242 B1	05/15/2001	Hata et al.			
	2	5,155,658	10/13/1992	Inam et al.			
	3	5,173,474	12/22/1992	Connell et al.			
	4	5,270,298	12/14/1993	Ramesh			
	5	5,358,925	10/25/1994	Neville Connell et al.			
	6	5,416,062	05/16/1995	Harada et al.			
	7	5,801,105	09/01/1998	Yano et al.			
	8	5,810,923	09/22/1998	Yano et al.			
	9	5,828,080	10/27/1998	Yano et al.			
	10	6,045,626	04/04/2000	Yano et al.			
	11	6,096,434	08/01/2000	Yano et al.			
	12	6,121,647	09/19/2000	Yano et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
	13	JP A 2000-332569 (with abstract and translation)	11/30/2000	Japan			
	14	JP A 2001-077102 (with abstract and translation)	03/23/2001	Japan			
	15	JP A 6-097452 (with abstract and translation)	04/08/1994	Japan			
	16	JP A 8-109099 (with abstract and translation)	04/30/1996	Japan			
	17	JP A 8-255790 (with abstract and translation)	10/01/1996	Japan			
	18	JP A 8-264524 (with abstract and translation)	10/11/1996	Japan			
	19	JP A 9-110592 (with abstract and translation)	04/28/1997	Japan			
	20	JP A 10-017394 (with abstract and translation)	01/20/1998	Japan			
EXAMINER					DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: August 21, 2003

	21	JP A 9-263494 (with abstract and translation)	10/07/1997	Japan		
	22	JP A 10-107216 (with abstract and translation)	04/24/1998	Japan		
	23	JP A 11-026296 (with abstract and translation)	01/29/1999	Japan		
	24	JP A 2000-101345 (with abstract and translation)	04/07/2000	Japan		
	25	JP A 2002-009358 (with abstract and translation)	01/11/2002	Japan		
	26	JP A 2001-122698 (with abstract and translation)	05/08/2001	Japan		
	27	JP A 10-265948 (with abstract and translation)	10/06/1998	Japan		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)						
	28	Fork et al., "Epitaxial yttria-stabilized zirconia on hydrogen-terminated Si by pulsed laser deposition", Appl. Phys. Letter 57, September 10, 1990, pp 1137-1139				
	29	Haakenaasen et al., "High quality crystalline YBa ₂ Cu ₃ O _{7-δ} films on thin silicon substrates", Appl. Phys. Lett. 64, March 21, 1994, pp 1573-1575				
	30	Hou et al., "Structure and properties of epitaxial Ba _{0.5} Sr _{0.5} TiO ₃ /SrRuO ₃ /ZrO ₂ heterostructure on Si grown by off-axis sputtering", Appl. Phys. Lett. 67, September 4, 1995, pp 1387-1389				
EXAMINER					DATE CONSIDERED	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						

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